SM12T1

ESD Protection Diode Array

Dual Common Anode

These dual monolithic silicon zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SOT−23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range − 12 V
- Standard Zener Breakdown Voltage Range − 13.3 V to 15.75 V
- Peak Power − 300 Watt (8 X 20 μs)
- Low Leakage
- Flammability Rating UL 94 V−0

Mechanical Characteristics:

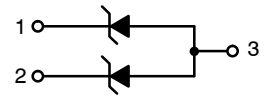
CASE: Void-free, transfer-molded, thermosetting plastic case
FINISH: Corrosion resistant finish, easily solderable
MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:
260°C for 10 Seconds
Package designed for optimal automated board assembly
Small package size for high density applications
Available in 8 mm Tape and Reel

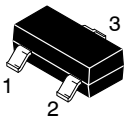
Use the Device Number to order the 7 inch/3,000 unit reel.
Replace the “T1” with “T3” in the Device Number to order the 13 inch/10,000 unit reel.

ON Semiconductor™

www.onsemi.com

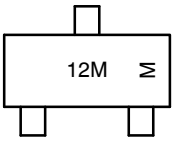
PIN 1. CATHODE
2. CATHODE
3. ANODE





SOT−23
CASE 318
STYLE 12

MARKING DIAGRAM



12M = Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping
SM12T1	SOT−23	3000/Tape & Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 20 μs (Note 1) @ $T_L \le 25°C$	P_{pk}	300	Watts
IEC 61000−4−2 (ESD) Air Contact		±15 ±8.0	kV
IEC 61000−4−4 (EFT)		40	A
IEC 61000−4−5 (Lightening)		12	A
Total Power Dissipation on FR−5 Board (Note 2) @ $T_A = 25°C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25°C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	− 55 to +150	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

1. Non−repetitive current pulse per Figure 3
2. FR−5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

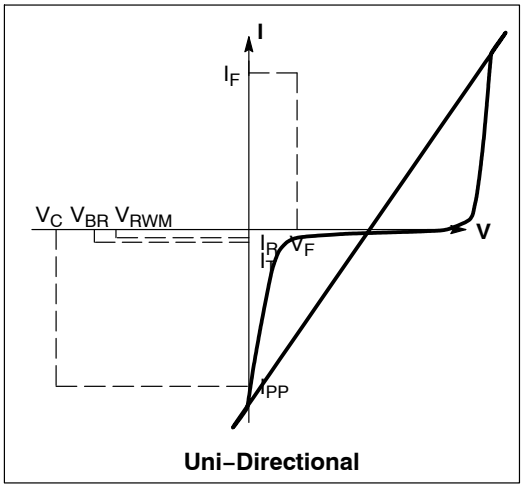
*Other voltages may be available upon request

ELECTRICAL CHARACTERISTICS

($T_A = 25°C$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



Uni−Directional

ELECTRICAL CHARACTERISTICS

Device	Device Marking	V_{RWM} (Volts)	I_R @ V_{RWM} (μA)	V_{BR}, Breakdown Voltage (Volts) Min	V_{BR}, Breakdown Voltage (Volts) Max	V_C @ I_{PP} = 1 Amp (Volts)	Max I_{PP} (Note 4) (Amps)	Typical Capacitance (pF) Pin 1 to 3 @ 0 Volts
SM12T1	12M	12	1.0	13.3	15.75	19	12	95

4. 8 × 20 μs pulse waveform per Figure 3

TYPICAL CHARACTERISTICS

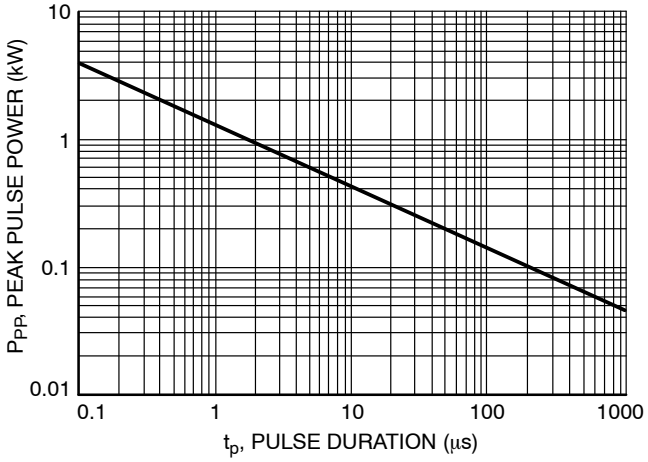


Figure 1. Non−Repetitive Peak Pulse Power versus Pulse Time

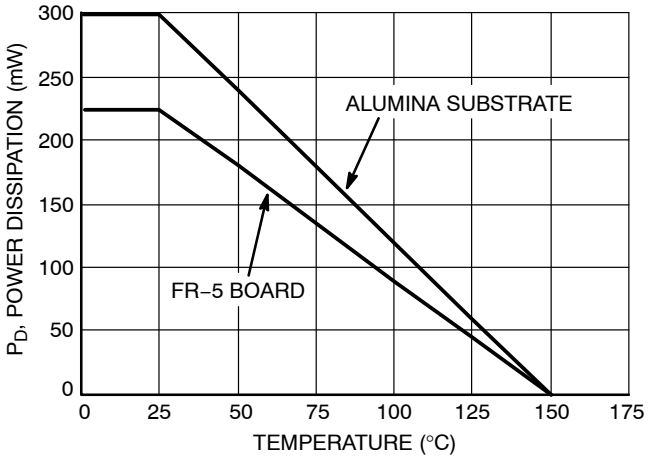


Figure 2. Steady State Power Derating Curve

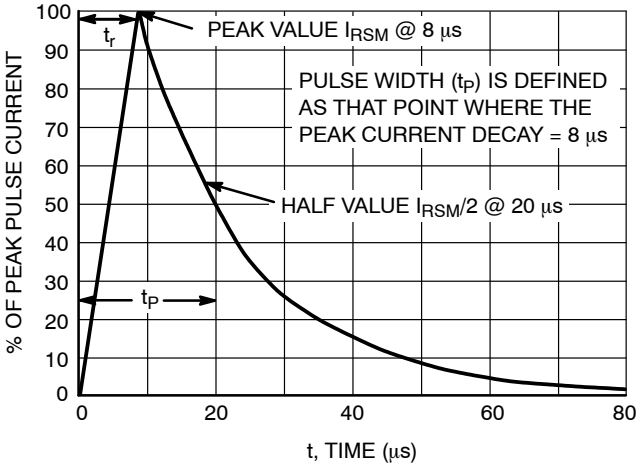


Figure 3. 8 × 20 μs Pulse Waveform

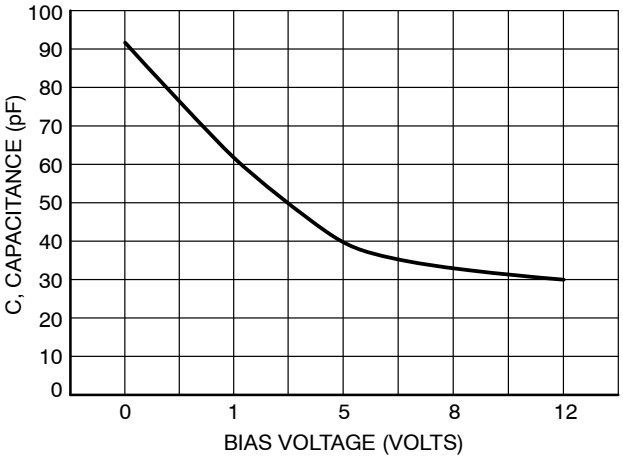
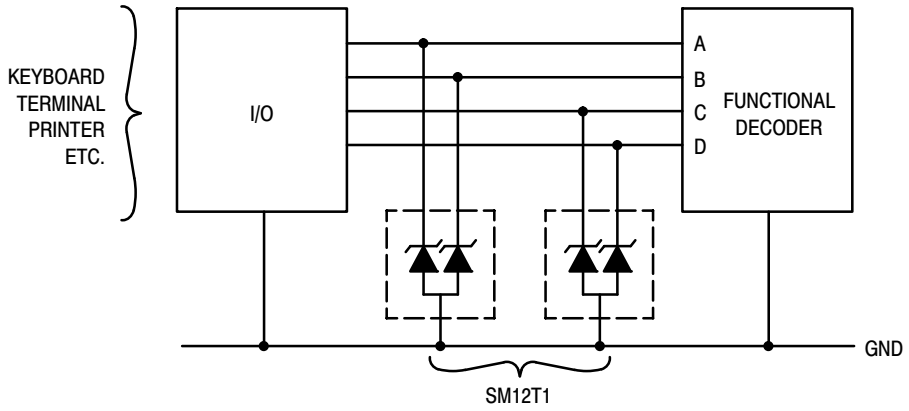


Figure 4. Typical Diode Capacitance

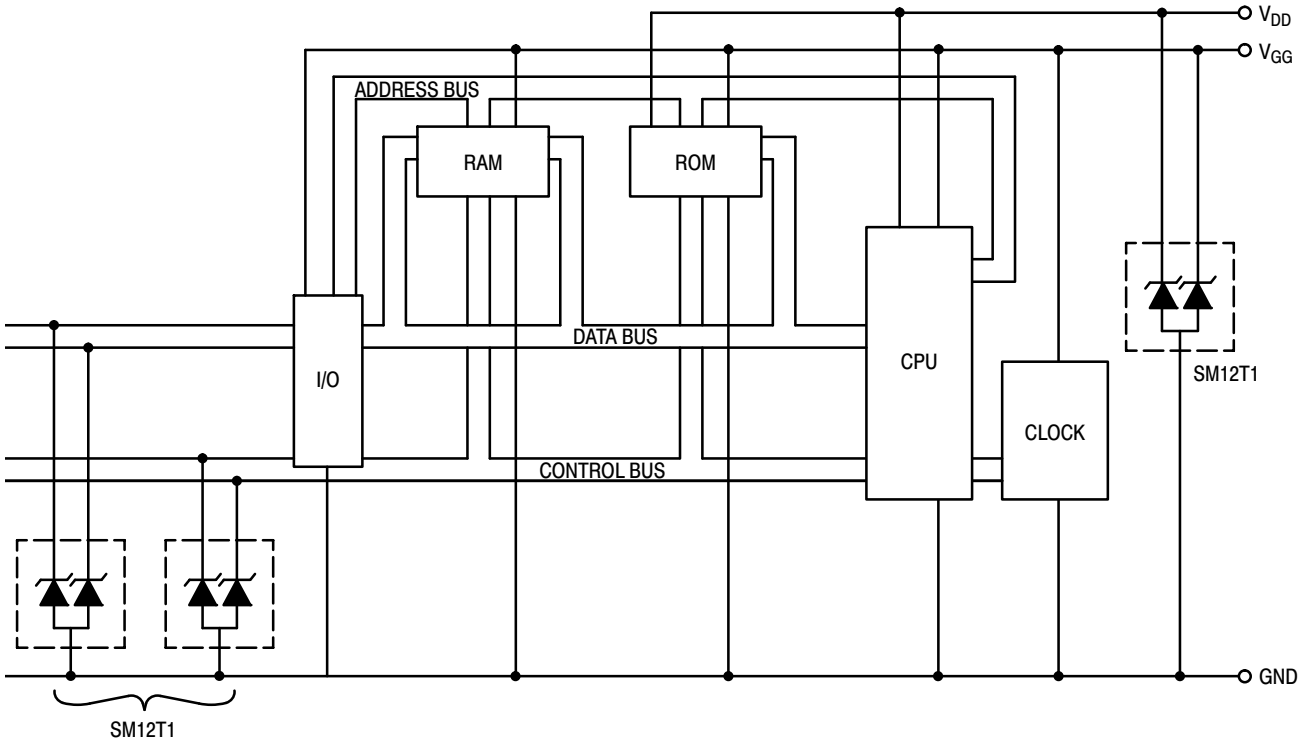
TYPICAL COMMON ANODE APPLICATIONS

A quad junction common anode design in a SOT−23 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially when board space is at a premium. Two simplified examples of surge protection applications are illustrated below.

Computer Interface Protection



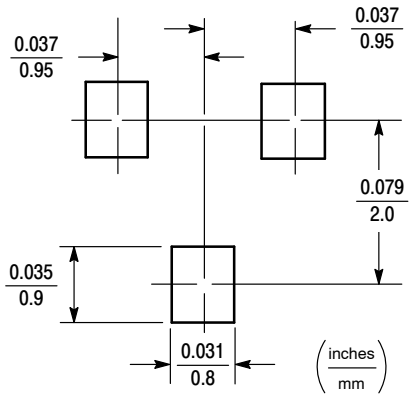
Microprocessor Protection



INFORMATION FOR USING THE SOT−23 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT−23

SOT−23 POWER DISSIPATION

The power dissipation of the SOT−23 is a function of the drain pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A. Using the values provided on the data sheet for the SOT−23 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_D = \frac{150°C - 25°C}{556°C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT−23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT−23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad®. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

SOLDERING PRECAUTIONS

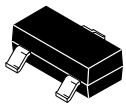
The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

Thermal Clad is a registered trademark of the Bergquist Company

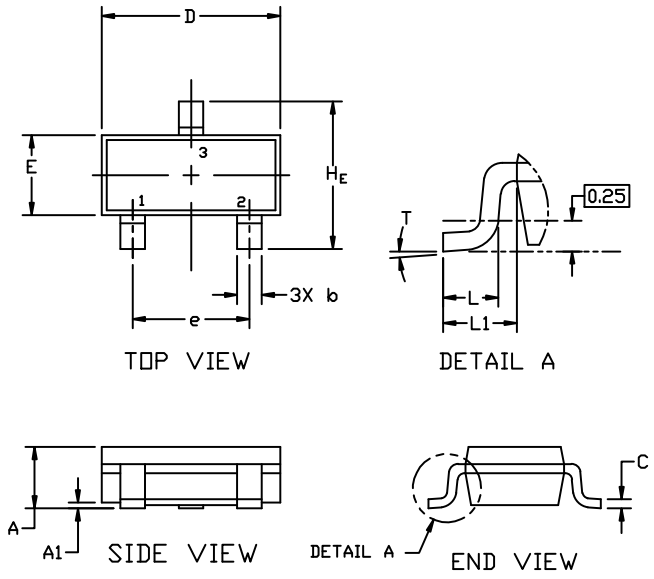
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 4:1

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

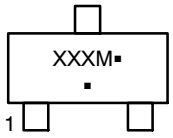


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

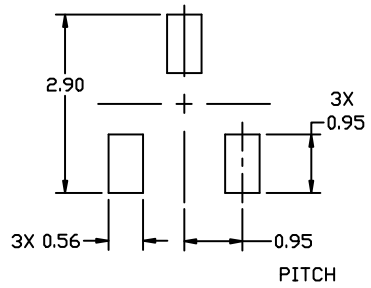
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOT−23 (TO−236)**		**PAGE 1 OF 2**

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

PUBLICATION ORDERING INFORMATION

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